PCN Number: 2023			30306002.2		PC	N Date:	March 07, 2023		
Title: Qualification of CFA bond wire Vertication			AB &	DFAB8 as additiona	l Fab sites,	Addi	tional A ⁻	T options, and Cu	
Cus	tomer	Contact:	<u>P</u>		<u>Manager</u>	Dept:	Dept:		uality Services
Proposed 1 st Ship Date: S						Sample requests Ap		opril 7, 2023*	
*Sa	mple r	equests rece	ived	afte	er April 7, 2023 wil	l not be su	ıppo	rted.	
Cha	nge Ty	pe:							
\boxtimes	Assem	bly Site		\boxtimes	Assembly Process		\boxtimes	Assem	bly Materials
	Desigr	า			Electrical Specifica	tion		Mecha	nical Specification
\boxtimes	Test S	ite			Packing/Shipping/I	abeling		Test P	rocess
□ Wafer Bump Site				Wafer Bump Mater	Wafer Bump Material		Wafer	Bump Process	
\boxtimes	Wafer	Fab Site		Χ	Wafer Fab Materials			Wafer	Fab Process
				Part number change					
PCN Details									

PCN Details

Description of Change:

Qualification of additional Fab sites (CFAB & DL-LIN) using qualified Process Technology and additional Assembly sites options for the list of devices in the product affected section below.

Curi	rent Fab Si	te	Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
DL-LIN	LBC3S	150mm	CFAB DL-LIN	LBC3S	200mm

Construction differences (No construction differences for Group 1) are as follows:

Group 2: CFAB & DFAB as an additional Fab sites and Cu as additional bond wire

	Current	Additional
Bond wire composition, diameter	Au, 0.96 mil	Cu, 0.96 mil

Group 3: CFAB & DFAB8 as additional fab sites and additional AT sites

	LEN	TAI	UTL1	CDAT	FMX	MLA
Mold Compound	SID #0011G60007	4205443 or 4211880	SID #C Z0135	4222198	4211880	4211649
Bond wire composition, diameter	Au, 1.0 mil	Au, 0.96 mil	Cu, 1.0 mil	Cu, 0.8 or 1.0 mil	Cu, 0.96	Cu, 0.96 mil
Mount Compound	SID #0003C10332	4208458 or 4147858	SID #PZ0037	4226215, or 4207123	4147858	4208458
Lead finish	N iPdA u	N iPdA u	N iPdA u	NiPdAu or Matte Sn	N iPdA u	NiPdAu
Final Test site	LEN	TAI	UTL2	CDAT	FM X	MLA

Group 4: CFAB as an additional Fab site and Cu as additional bond wire

	Current	Additional
Bond wire composition,	Au, 0.96 mil	Cu, 0.96 mil
diameter		

Group 5: CFAB as an additional Fab site and additional AT sites							
	LEN	TAI	UTL1	CDAT	FMX	MLA	
Texas Instruments Incorporated	TI Information - Selective Disclosure			PC N202303	306002.2		

Mold Compound	SID #0011G60007	4205443 or 4211880	SID #CZ0135	4222198	4211880	4211649
Bond wire composition, diameter	Au, 1.0 mil	Au, 0.96 mil	Cu, 1.0 mil	Cu, 0.8 or 1.0 mil	Cu, 0.96	Cu, 0.96 mil
M ount C ompound	SID #0003C10332	4208458 or 4147858	SID #PZ0037	4226215 or 4207123	4147858	4208458
Lead finish	N iPdA u	NiPdAu	NiPdAu	NiPdAu or Matte Sn	NiPdAu	NiPdAu
Final Test site	LEN	TAI	UTL2	CDAT	FM X	MLA

Probe site change: All devices listed in this notification will also be qualified at CD-PR as an additional probe site with the following exceptions: MAX3232EIPWRQ1 & TRS3232EQPWRQ1 (these devices have no probe step)

Upon expiry of this PCN TI will combine lead free solutions in a single <u>standard part number</u>, for the devices in groups 3 & 5. For example; <u>TLV2374QDRQ1</u> – can ship with both Matte Sn and NiPdAu/Ag.

Example:

- Customer order for 7500 units of TLV2374QDRQ1with 2500 units SPQ (Standard Pack Quantity per Reel).
- TI can satisfy the above order in one of the following ways.
 - I. 3 Reels of NiPdAu finish.
 - II. 3 Reels of Matte Sn finish
 - III. 2 Reels of Matte Sn and 1 reel of NiPdAu finish.
 - IV. 2 Reels of NiPdAu and 1 reel of Matte Sn finish.

Qual details are provided in the Qual Data Section.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
🛛 No Change	🛛 No Change	🛛 No Change	🛛 No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
CFAB	CU3	CHN	Chengdu

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TAI	TAI	TWN	Chung Ho, New Taipei City
LEN	LIN	TWN	Taichung

UTL1	NSE	THA	Bangkok
CDAT	CDA	CHN	Chengdu
TI Malaysia	MLA	MYS	Kuala Lumpur
FMX	MEX	MEX	Aguascalientes

Sample product shipping label (not actual product label)



Product Affected:

Group 1 (CFAB & DFAB8 as additional Fab sites)Device list: TLV2462QDGKRQ1

Group 2 (CFAB & DFAB as an additional Fab sites and Cu as additional bond wire)Device list:

TLC2264AIDRCT	TLV2374QDRG4Q1	TLV2462QDRG4Q1	TLV2474QDRG4Q1
TLC2264AQPWRG4Q1	TLV2374QDRQ1	TLV2462QDRQ1	TLV2474QDRQ1
TLC2264AQPWRQ1	TLV2374QPWRG4Q1	TLV2462QPWRG4Q1	TLV272QDRQ1
TLV2264AQPWRQ1	TLV2374QPWRQ1	TLV2463AQPWRG4Q1	TLV274QDRQ1
TLV2371QDRG4Q1	TLV2374QPW RRB	TLV2474AQDRG4Q1	TLV274QPWRG4Q1
TLV2372QDRQ1	TLV2462AQDRQ1		

Group 3 (CFAB & DFAB8 as additional fab sites and additional AT sites) Device list:

TLC072QDRQ1	TLV2371QDBVRQ1	TLV271QDBVRQ1	TPS3838E18QDBVRCT		
TLC084QPWPRQ1	TLV2474APWPRQ1	TLV271QDBVRVS	TPS3838K33QDBVRQ1		
TLV2264AQD	TLV2474QPWPRQ1				

Group 4 (CFAB as an additional Fab site and Cu as additional bond wire)Device list:

MAX3232EIPW RQ1	MLA00464PWR	TLC2272MDRCT	TLC2272SDRG4SV
MLA00059DR	TLC2272AQDR	TLC2272QDRG4Q1	TLC2274AQDRG4Q1
MLA00060DR	TLC2272AQDRG4	TLC2272QDRQ1	TLC2274AQDRQ1
MLA00172DR	TLC2272AQDRG4Q1	TLC2272QDRSV	TLC2274AQPWRG4Q1
MLA00349PWR	TLC2272AQDRQ1	TLC2272QPWRG4	TLC2274AQPWRQ1
MLA00351PWR	TLC2272AQPWRG4Q1	TLC2272QPWRG4Q1	TLC2274ASDRDL
MLA00354DR	TLC2272AQPWRQ1	TLC2272QPWRQ1	TLC2274QPWRQ1
MLA00361PWR	TLC2272ASPW RCT	TLC2272QPWRSV	TRS3232EQPWRQ1
MLA00402PWR			

Group 5 (CFAB as an additional Fab site and additional AT sites) Device list:								
TLC2272AMD	TLC2272AMDRG4	TLC2274AMD	TLC2274AQDRG4					

TLC2272AMDR TLC2272MDR TLC2274AMDG4

	TI Informational Selective Disclosure
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Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approved 2-March-2023

Product	Attributes
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Attributes	Qual Device: TLC2264AQPWRQ1	QBS Process Reference: TPS3838E18QDBVRCT	QBS Package Reference: SN3257QPWRQ1	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	
Operating Temp Range	-40C to 125C	-40C to 125C	-40C to 125C	
Product Function	Signal Chain	Interface	Interface	
Wafer Fab Supplier	CFAB	CFAB	RFAB	
Assembly Site	MLA	CDAT	MLA	
Package Type	TSSOP	SOT-23	TSSOP PW	
Package Designator	D	DBV		
Ball/Lead Count	14	5	16	

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: TLC2264AQPWRQ1	QBS Process Reference: TPS3838E18QDBVRCT	
Τe	st Group /	A – Acc	celerated Environment Stress Test	8						
	PC	A1	JEDEC J-STD-020 JESD22- A113	3	231	Automotive Preconditioning	Level 1-260C	-	Pass	Pass
	bHAST	A2	JEDEC JESD22-A101	3	77	Biased HAST, 130C/85%RH	192 Hours	-	3/231/0	3/210/0
	AC	A3	JEDEC JESD22-A102	3	77	Autoclave, 121C	192 Hours	-	3/231/0	3/231/0
	тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	-	3/231/0	3/231/0
	TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	2000 Cycles	-	-	3/210
	HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Life, 175C	500 Hours	-	1/45/0	3/135/0
	HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Life, 175C	1000 Hours	-	-	3/132/0
Τe	st Group E	B – Acc	elerated Lifetime Simulation Tests	\$						
	HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	1/77/0	3/231/0	-
	ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	3/2400/0	-
Τe	st Group (C – Pac	kage Assembly Integrity Tests							
	WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	3/90/0	3/90/0
	WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	3/90/0	3/90/0
	SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability >95% Lead Coverage	15	-	1/15/0	-
	PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	10 units	1/10/0	3/30/0	-
Τe	st Group I	D – Die	Fabrication Reliability Tests							
	EM	D1	JESD61	-	-	Electromigration		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	-
	TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	нсі	D3	JESD60 & 28	-	-	Hot Injection Carrier		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	NBTI	D4	-	-	-	Negative Bias Temperature Instability		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Te	st Group I		ctrical Verification Tests							
	HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0	-
	CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	1/3/0	1/3/0	-
	LU	E4	AEC Q100-004	1	6	Latch-up	+/100mA, 125C	1/6/0	1/6/0	-
	ED	E5	AEC Q100-005	3	30	Electrical Distribution	Cpk > 1.67	1/30/0	3/90/0	-

- QBS: Qual By Similarity - Qual Device TLC2264AQPWRQ1 is qualified at LEVEL1-260C

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

 Ambient Operating Temperature by Automotive Grade Level:
 Grade 0 (or E): -40°C to +150°C
 Grade 1 (or Q): -40°C to +125°C
 Grade 2 (or T): -40°C to +105°C
 Grade 3 (or I): -40°C to +85°C
 Grade 3 (or I): -40°C to +

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB/ HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/UHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20200903-135990



TI Information Selective Disclosure

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approved 2-March-2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN65HVDA195QDRQ1
Te	st Group A							
	PC	A1	JEDEC J-STD-020 JESD22- A113	3	231	Automotive Preconditioning	Level 1-260C	Pass
	bHAST	A2	JEDEC JESD22-A101	3	77	Biased HAST, 130C/85%RH	192 Hours	3/231/0
	AC	A3	JEDEC JESD22-A102	3	77	Autoclave, 121C	192 Hours	3/231/0
	тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
	HTSL	Aß	JEDEC JESD22-A103	1	45	High Temp. Storage Life, 175C	500 Hours	1/45/0
Te	st Group B	3 – Acc	elerated Lifetime Simulation Tests	;				
	HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	3/231/0
	ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	3/2400/0
Te	st Group (C – Pac	kage Assembly Integrity Tests					
	WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	3/90/0
	WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	3/90/0
	SD	СЗ	JEDEC JESD22-B102	1	15	Surface Mount Solderability >95% Lead Coverage	15	1/15/0
	PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	10 units	3/30/0
Te	st Group [) – Die	Fabrication Reliability Tests					
	EM	D1	JESD81	-	-	Electromigration	-	Completed Per Process Technology Requirements
	TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirements
	нсі	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements
	NBTI	D4	-	-	-	Negative Bias Temperature Instability		Completed Per Process Technology Requirements
	SM	D5	-	-	-	Stress Migration		Completed Per Process Technology Requirements

Te	Test Group E – Electrical Verification Tests									
	HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0		
	CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	1/3/0		
	LU	E4	AEC Q100-004	1	6	Latch-up	+/100mA, 125C	1/6/0		
	ED	E5	AEC Q100-005	3	30	Electrical Distribution	Cpk > 1.67	3/30/0		

- QBS: Qual By Similarity - Qual Device TPS3838E18QDBVRCT is qualified at LEVEL1-260C

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: R-CHG-2211-005



Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approve Date 11-Feb-2020 Updated 02/11/2020-Added QBS Data

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TLV2401QDBVRQ1</u>	QBS Process Reference: MAX3243IPWG4DL
			Test Gi						
	PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning Level 1	Level 1-260C	3/1199/0	-
	HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0
	AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	3/231/0	3/231/0
	тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-
	HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 150C	1000 Hours	-	3/231/0
	HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 Hours	3/135/0	-
			Test G	roup B – A	locelerate	d Lifetime Simulation Tests			
	HTOL	В1	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	3/231/0	3/231/0
	ELFR	В2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	3/2400/0
	EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-
			Test	Group C -	- Package	Assembly Integrity Tests			
	WBP	C1	AEC Q100-001	1	30	Bond Pull, over ball	Minimum of 5 devices, 30 wires Cpk>1.67	3/90/0	1/30/0
\prod	WBP	C1	AEC Q100-001	1	30	Bond Pull, over stitch	Minimum of 5 devices, 30 wires Cpk>1.67	3/90/0	1/30/0
	WBS	C1	AEC Q100-001	1	30	Auto Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	3/90/0	-
				Qual Device:	QBS Process				

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TLV2401QDBVRQ1</u>	QBS Process Reference: <u>MAX3243IPWG4DL</u>
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	1/15/0	-
SD	С3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	3/30/0	3/30/0
LI	C6	JEDEC JESD22-B105	1	22	Lead Pull to Destruction	Leads	1/22/0	-
		Tes	t Group D	– Die Fab	rication Reliability Tests			
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
		T	est Group	E – Electr	rical Verification Tests			
нвм	E2	AEC Q100-002	1	3	ESD - HBM - Q100	500 V (1)	1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-up	Per AEC-Q100-004	1/6/0	-
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67	3/90/0	-

- QBS: Qual By Similarity - Qual Device TLV2401QDBVRQ1 is qualified at LEVEL1-260C A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green Note (1): See ESD waiver attached to eQDB. Change Number: NA TI Qualification ID: 20190124-128331



TI Information Selective Disclosure

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Q006 Qual Summary for LBC3 BOAC with PCC wire in FMX with 150mm wafers (ALSiCu metalization) Q100H (Grade 1, -40/125C) Approved 07-Sep-2016

Product Attributes

Attributes	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C	
Product Function	Interface	Interface	Interface	
Wafer Fab Supplier	DFAB	DFAB	DFAB	
Die Revision	A	A	A	
Assembly Site	FMX	FMX	FMX	
Package Type	SOIC	SOIC	SOIC	
Package Designator	D	D	D	
Ball/Lead Count	8	8	8	

- QBS: Qual By Similarity
- QUal Device SN65HVD233QDRQ1, Qual Device SN65HVD235QDRQ1, - Qual Device SN65HVD234QDRQ1 is qualified at LEVEL1-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1
		Test Group A –	Accelerate						
-	-	-	-	-	SAM Analysis Post Precon	Completed	1/22/0	1/22/0	1/22/0
PC	A1	JEDEC J-STD-020 JESD22-A113	-	-	Preconditioning	Level 1- 260C	No Fails	No Fails	No Fails
-	-	-	-	-	SAM Analysis Post Precon	Completed	1/22/0	1/22/0	1/22/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST 130C/85%RH	96 Hours	1/77/0	1/77/0	1/77/0
-	-	-	3	1	Cross Section Post bHAST 96 Hours	Completed	1/1/0	1/1/0	1/1/0

				Min	SS/			Qual Device:	Qual Device:	Qual Device:
	Туре	#	Test Spec	Lot Qty	Lot	Test Name / Condition	Duration	SN65HVD233QDRQ1	SN65HVD234QDRQ1	SN65HVD235QDRQ1
	-	-	-	3	22	SAM Analysis Post bHAST 96 Hours	Completed	1/22/0	1/22/0	1/22/0
	-	-	-	3	30	Wire Bond Shear Post bHAST 96 Hours	Wires	1/30/0	1/30/0	
	-	-	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	1/30/0	1/30/0	-
	-	-	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	1/30/0	1/30/0	-
	HAST	A2	JEDEC JESD22-A110	3	70	Biased HAST 130C/85%RH	192 Hours	1/70/0	1/70/0	1/70/0
	-	-	-	3	1	Cross Section Post bHAST 192 Hours	Completed	1/1/0	1/1/0	1/1/0
	-	-	-	3	22	SAM Analysis Post bHAST 192 Hours	Completed	1/22/0	1/22/0	1/22/0
	-	-	-	3	30	Wire Bond Shear Post bHAST 192 Hours	Wires	1/20/0 (1)	1/30/0	1/30/0
	-	-	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	1/30/0	1/30/0	1/30/0
	-	-	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	1/20/0 (1)	1/30/0	1/30/0
	TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle -65/150C	500 Cycles	1/77/0	1/77/0	1/77/0
	-	-	-	3	1	Cross Section Post T/C 500 Cycles	Completed	1/1/0	1/1/0	1/1/0
	-	-	-	3	22	SAM Analysis Post T/C 500 Cycles	Completed	1/22/0	1/22/0	1/22/0
	TC- WBS	-	-	3	30	Wire Bond Shear Post T/C 500 Cycles	Wires	1/30/0	1/30/0	1/30/0
	TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	1/30/0	1/30/0	1/30/0
	TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	1/30/0	1/30/0	1/30/0
	тс	A4	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle -65/150C	1000 Cycles	1/70/0	1/70/0	1/70/0
		-	-	3	1	Cross Section Post T/C 1000 Cycles	Completed	1/1/0	1/1/0	1/1/0
		-	-	3	22	SAM Analysis Post T/C 1000 Cycles	Completed	1/22/0	1/22/0	1/22/0
	TC- WBS	-	-	3	30	Wire Bond Shear Post T/C 1000 Cycles	Wires	1/30/0	1/30/0	1/30/0
	TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Ball Post T/C 1000 Cycles	Wires	1/30/0	1/30/0	1/30/0
	TC- WBP	A4	MIL-STD883 Method 2011	3	30	Bond Pull over Stitch Post T/C 1000 Cycles	Wires	1/30/0	1/30/0	1/30/0
	Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN65HVD233QDRQ1	Qual Device: SN65HVD234QDRQ1	Qual Device: SN65HVD235QDRQ1
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	1000 Cycles	N/A	N/A	N/A
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	2000 Cycles	N/A	N/A	N/A
	HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake	1000 Hours	1/45/0	1/45/0	1/45/0
	-	-	-	3	1	Cross Section Post Bake 1000 Hours	Completed	1/1/0	1/1/0	1/1/0
	HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	1/44/0	1/44/0	1/44/0
	-	-	-	3	1	Cross Section Post Bake 2000 Hours	Completed	1/1/0	1/1/0	1/1/0
T	est Group	C – P	ackage Assembly Integri	ty Tests						
	WBS	C1	AEC Q100-001	3	30	Wire Bond Shear Cpk>1.67	Wires	1/30/0	1/30/0	1/30/0
	WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull Cpk>1.67	Wires	1/30/0	1/30/0	1/30/0
<u> </u>									•	

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Junction Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/HoU/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20160217-116814

Notes/ Comments: (1) Performed on only 2 devices



Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

SN3257QPWRQ1 (Grade 1, Q100H, -40/125C) Approved 13-Feb-2020

Product Attributes

Attributes	Qual Device: <u>SN3257QPWRQ1</u>	QBS Process Reference: <u>SN3257QDYYRQ1</u>
Automotive Grade Level	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C
Product Function	Interface	Interface
Wafer Fab Supplier	RFAB	RFAB
Die Revision	A	A
Assembly Site	MLA	PHI
Package Type	TSSOP	SOT-23
Package Designator	PW	DYY
Ball/Lead Count	16	16

- QBS: Qual By Similarity

- Qual Device SN3257QPWRQ1 is qualified at LEVEL1-260C

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as: Number of lots / lotal sample size / lotal failed								
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: <u>SN3257QPWRQ1</u>	QBS Process Reference: <u>SN3257QDYYRQ1</u>	
		Test Group A – A	ccelerat	ed Envi	ironment Stress Tests				
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	Level 1- 260C	No Fails	-	
HAST	A2	JEDEC JESD22-A110	з	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-	
AC	A3	JEDEC JESD22-A102	з	77	Autoclave 121C	96 Hours	3/231/0	-	
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, - 55/150C	1000 Cycles	3/231/0	-	
TC- WBP	A4	MIL-STD883 Method 2011	1	60	Bond Pull Post Temp Cycle	Wires	1/60/0	-	
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-	
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 Hours	3/135/0	-	
		Test Group B – A	ccelerat	ted Life	time Simulation Tests				
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	300 Hours	3/231/0	3/231/0	
ELFR	В2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0	
EDR	в3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-	
		Test Group C –	Packag	e Asse	mbly Integrity Tests				
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear, Cpk >1.67	Wires	3/90/0	-	
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull, Cpk >1.67	Wires	3/90/0	-	
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	PB Solder	1/15/0	-	
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free Solder	1/15/0	-	
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	3/30/0	-	
		Test Group D	– Die Fa	bricatio	on Reliability Tests				
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-	
TDDB	D2	JESD35	-	-	Time Dependant Completed Dielectric Brackdown - Techr		Completed Per Process Technology Requirements	-	
нсі	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-	
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-	
SM	D5	-	-	-	Stress Migration -		Completed Per Process Technology Requirements	-	

Test Group E – Electrical Verification Tests										
HBM	E2	AEC Q100-002	1	3	ESD - HBM	5000 V	1/3/0	-		
CDM	E3	AEC Q100-011	1	3	ESD - CDM	2000 V	1/3/0	-		
LU	E4	AEC Q100-004	1	6	Latch-up	Per AEC Q100-004	1/6/0	-		
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk >1.67	3/90/0	-		

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20190311-128972

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Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Q100H Grade-1 qual for TLV27L2QDRQ1 (DFAB/LBC3S) in FMX using 8-pin SOIC pkg

Approved 03-Sep-2015 Updated 08/03/2015-Added QBS Data Product Attributes

			Troduct Attrib	utes		
Attributes	Qual Device: TLV2372QDRG4Q1	Qual Device: TLV2372QDRQ1	Qual Device: TLV27L2QDRQ1	QBS Process Reference: MAX3243IPWG4DL	QBS Package Reference: SN65HVD230D	QBS Package Reference: TPS28225TDRQ1
Operating Temp Range	-40°C to +125°C	-40°C to +125°C	-40°C to +125°C	-40°C to +125°C	-40°C to +125°C	-40°C to +105°C
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 2
Product Function	Signal Chain	Signal Chain	Signal Chain	-	-	-
Wafer Fab Supplier	DFAB	DFAB	DFAB	DFAB	DFAB	DMOS5
Die Revision	A	A	A	A	В	D
Assembly Site	FMX	FMX	FMX	MLA	FMX	FMX
Package Type	SOIC	SOIC	SOIC	TSSOP	SOIC	SOIC
Package Designator	D	D	D	PW	D	D
Ball/Lead Count	8	8	8	28	8	8
ORC: Out Du Cimilarity						

- QBS: Qual By Similanty
 - Qual Devices qualified at LEVEL1-260C: TLV2372QDRG4Q1, TLV2372QDRQ1, TLV27L2QDRQ1

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

QBS Packag QBS Process BS Packa Qual Device: TLV2372QDRG4Q1 Qual Device: TLV27L2QDRQ1 Test Spec Lot SS/ Lot Test Name / Condition Qual Device: TLV2372QDRQ1 Туре Duratio # Reference: MAX3243IPWG4DL Reference: TP S28225TDRQ1 SN65HVD230D Automotive 020 JESD22-1/243/0 1/300/0 PC 1 0 Level 3-260C 1/240/0 A1 Preconditioning A113 Biased Temperature JEDEC JESD22тнв A2 3 and Humidity 85C/85%RH 1000 Hours 1/77/1 (Note 1) 1/77/0 A101 JEDEC JESD22-Biased HAST 1 HAST A2 77 96 Hours 1/77/0 3/231/0 A110 JEDEC JESD22-130C/85%RH 96 Hours AC A3 1 77 Autoclave 121C 1/77/0 1/77/0 1/77/0 3/231/0 A102 JEDEC JESD22-Temperature Cycle, тс A4 A104 and 1 77 500 Cycles 1/77/0 1/77/0 1/77/0 3/231/0 -. 65/150C Appendix 3 MIL-STD883 Post Temp Cycle Bond 30 TC-BF 1 Wires 1/30/0 Method 2011 JEDEC JESD22-Pull Power Temperature PTC A5 1 1000 Cycles N/A N/A N/A Cycle, -40/105C High Temp. Storage A105 JEDEC JESD22-HTSL A6 1 45 1000 Hours 1/45/0 -A103 JEDEC JESD22-Bake, 150C High Temp. Storage Bake, 175C HTSL A6 1 45 500 Hours 1/45/0 A103 Test Group B – Acc erated Lifeti Tests JEDEC JESD22 HTOL B1 1 77 Life Test, 150C 408 Hours 1/77/0 1/77/0 1/77/0 3/231/0 A108 Early Life Failure Rate, ELFR B2 AEC Q100-008 3 48 Hours 1/800/0 125C Early Life Failure Rate ELFR B2 AEC Q100-008 3 48 Hours 2/1600/0 -150 NVM Endurance, Data B3 AEC Q100-005 3 N/A N/A EDR Retention, and Operational Life N/A

Test Group C – Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	-	-	1/30/0	-	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	-	-	1/30/0	-	-	-
SD	C3	JEDEC JESD22- B102	1	15	Surface Mount Solderability	Pb	-	-	-	-	-	1/15/0
SD	C3	JEDEC JESD22- B102	1	15	Surface Mount Solderability	Pb-Free	-	-	-	-	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3		Physical Dimensions (Cpk>1.67)		-	-	-	3/30/0	3/30/0	-
Test Grou	ıр Е − Е	lectrical Verification	Tests									
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	-	-	1/3/0	-	-	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	-	-	1/3/0	-	-	-
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC-Q100- 004)	-	-	1/6/0	-	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67	-	-	3/90/0	-	-	-
A1 (DC): D												

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Junction Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +125°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

Note (1): Die EOS, 1 unit - capacitor pinhole, discounted (QTS 439122-1)

TI Qualification ID: 20150513-113887

Affected ZVEI IDs: SEM-PW-02, SEM-PW-13, SEM-PA-05, SEM-PA-07, SEM-PA-08, SEM-PA-11, SEM-TF-01

For alternate parts with similar or improved performance, please visit the product page on $\underline{\text{TI.com}}$

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